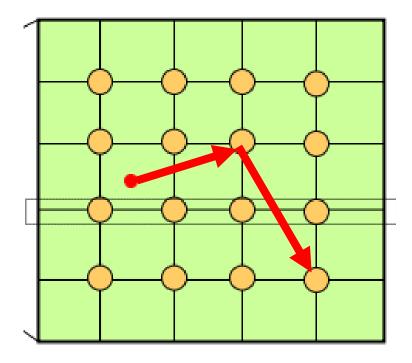
ECE 340: Semiconductor Electronics

Chapter 1: Crystal Properties and Growth of Semiconductors

Wenjuan Zhu

Why do we need to study crystal structure?

 Because the transport of charge through a metal or semiconductor depends on the arrangement of atoms in the solid



Material types by electrical resistivity

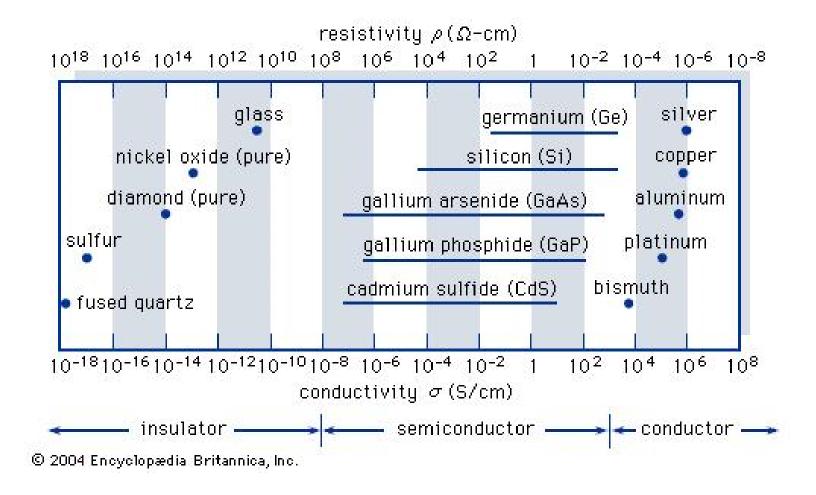
- Insulators: very high resistivity
 - Diamond (SiO2)
 - Electric Resistivity = 1018 Ω m
- Metals: very low resistivity
 - Gold (Au)
 - Electric Resistivity = 22.14 nΩ m
- Semiconductors: intermediate resistivity
 - Silicon (Si)
 - Electric Resistivity = 103 Ω m







• Where semiconductors fit in (electrically):



Semiconductor material

Table 1-1 Common semiconductor materials: (a) the portion of the periodic table where semiconductors occur; (b) elemental and compound semiconductors.

(a)	II	III	IV	V	VI
		В	С	Ν	
		Al	Si	P	S
	Zn	Ga	Ge	As	Se
	Cd	ln		Sb	Те
			Binary III–V	Binary II–VI	
(b)	Elemental	IV compounds	compounds	compounds	
	Si	SiC	AlP	ZnS	
	Ge	SiGe	AlAs	ZnSe	
			AlSb	ZnTe	
			GaN	CdS	
			GaP	CdSe	
			GaAs	CdTe	
			GaSb		
			InP		
			InAs		
			InSb		

Structure types in solid material

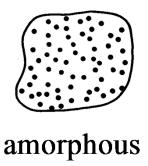
 Crystalline: atoms are ordered into a well-defined lattice that extends over very long distances;



 Polycrystalline: consist of many small regions of single-crystal material;



Amorphous: no periodic structure;



Primitive Cell and Unit Cell

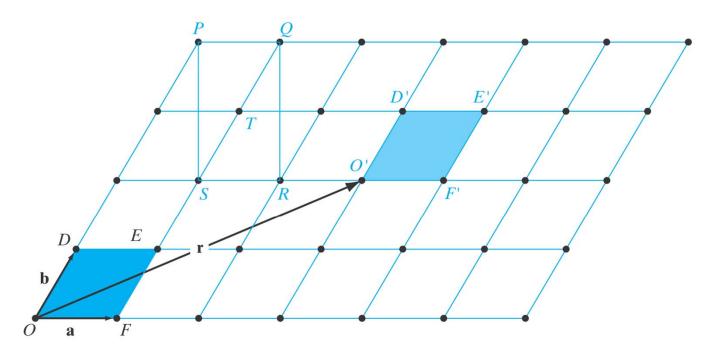
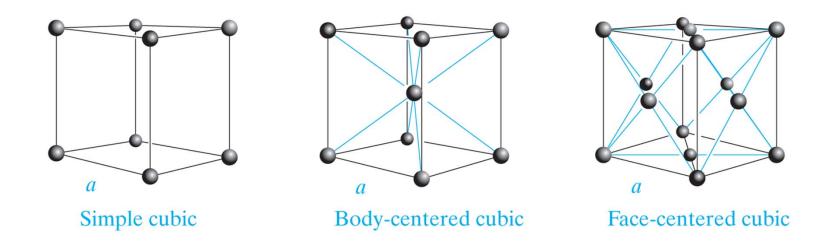


Figure 1.2

A two-dimensional lattice showing translation of a unit cell by $\mathbf{r} = 3\mathbf{a} + 2\mathbf{b}$.

Primitive cell: smallest cell, ODEF.
 Unit cells: allowing center lattice points, PQRS with center T

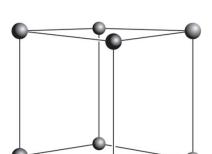
Unit Cell - Cubic Lattice



a is called lattice constant.

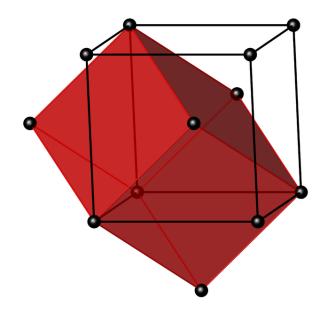
Primitive cell

Simply cubic

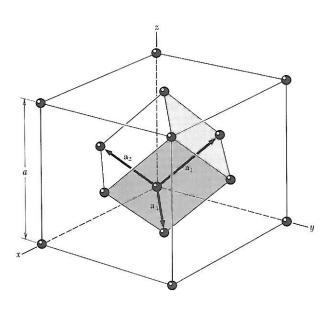


Simple cubic

Body-centered cubic

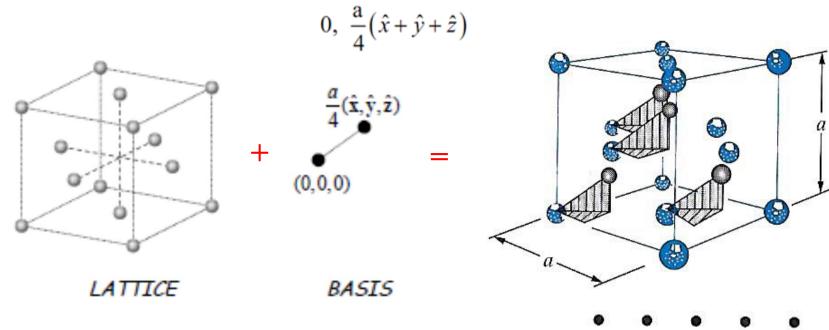


Face-centered cubic

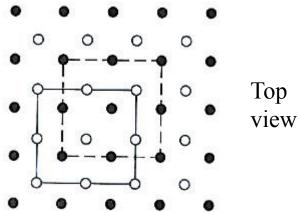


Diamond Lattice

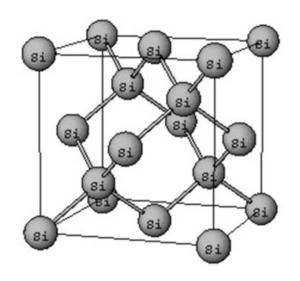
• Diamond structure can be described as an FCC lattice with a 2 atom basis.



- 2 atom basis to a FCC lattice
- Tetrahedral bond arrangement
- Each atom has 4 nearest neighbors
- Elements crystallizing in the diamond structure are: C, Si, Ge

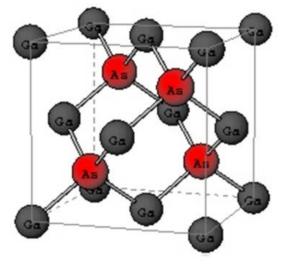


Diamond Lattice vs. Zinc Blende



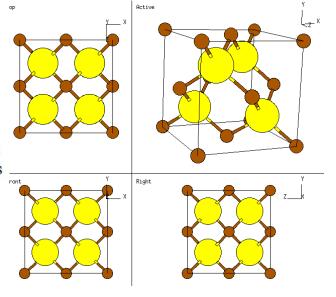
Silicon

Diamond Cubic Structure
4 atoms at (0,0,0)+FCC translations
4 atoms at (1/4,1/4,1/4)+FCC translations
Bonding: covalent

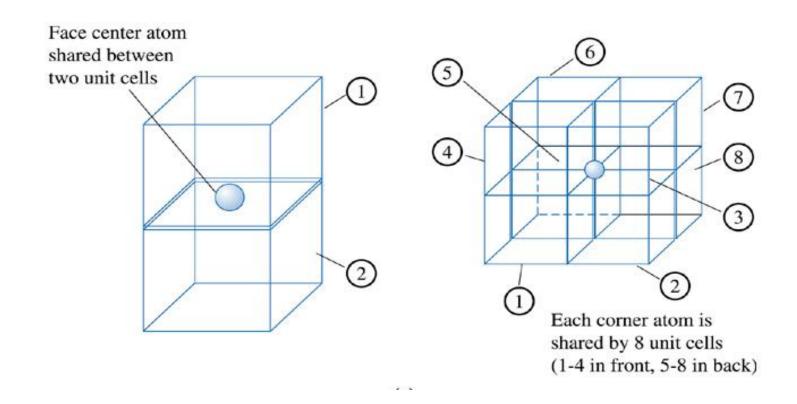


GaAs

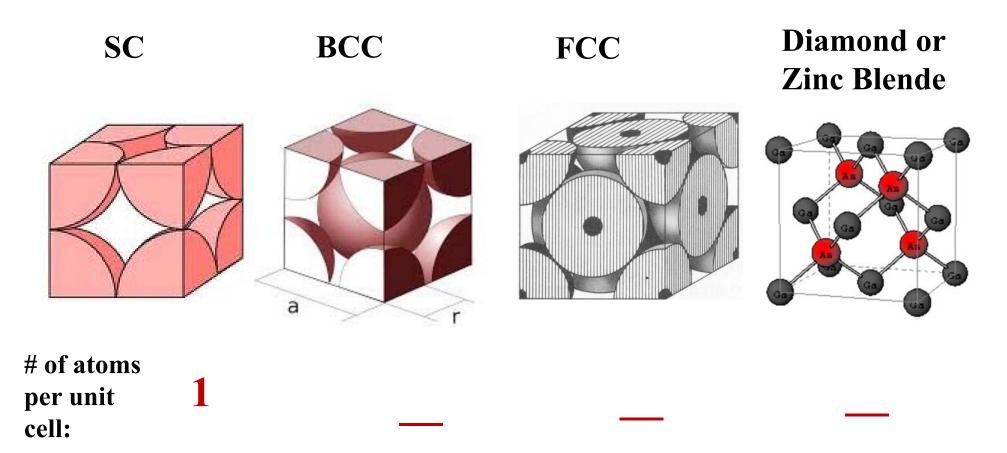
ZnS (Zinc Blende) Structure 4 Ga atoms at (0,0,0)+ FCC translations 4 As atoms at (1/4,1/4,1/4)+FCC translations Bonding: covalent, partially ionic



Number of Atoms per Unit Cell



Number of Atoms per Unit Cell



Nearest Neighbor

SC BCC FCC Zinc Blende

of nearest neighbor:

6

nearest neighbor distance:

a

Density Calculations:

ATOMIC DENSITY: Number of Atoms per Unit Volume

$$\frac{\text{\# atoms}}{\text{cm}^3} = \frac{\mathbf{n}}{\mathbf{V_c}} = \frac{\text{\# atoms/unit cell}}{\text{Volume/unit cell}}$$

MASS DENSITY:
$$\rho = \frac{\text{Mass of Atoms in Unit Cell}}{\text{Total Volume of Unit Cell}}$$

Theoretical Density

atoms/unit cell
$$\rho = \frac{n A}{V_c N_A}$$
 Atomic weight (g/mol)

Volume/unit cell $V_c N_A$ Avogadro's number (cm³/unit cell) (6.023 x 10²³ atoms/mol)

Avogadro constant is defined as the number of constituent particles (usually atoms or molecules) per mole of a given substance

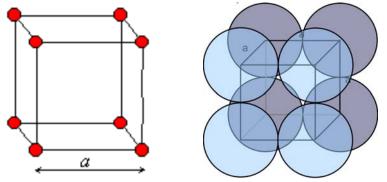
Atomic density

Diamond or **FCC** SC **BCC** Zinc Blende **Atomic** density:

Packing Density Fraction

Packing density fraction, or atomic packing factor (APF), is the fraction of a volume filled with atoms, when atoms are close-packed.

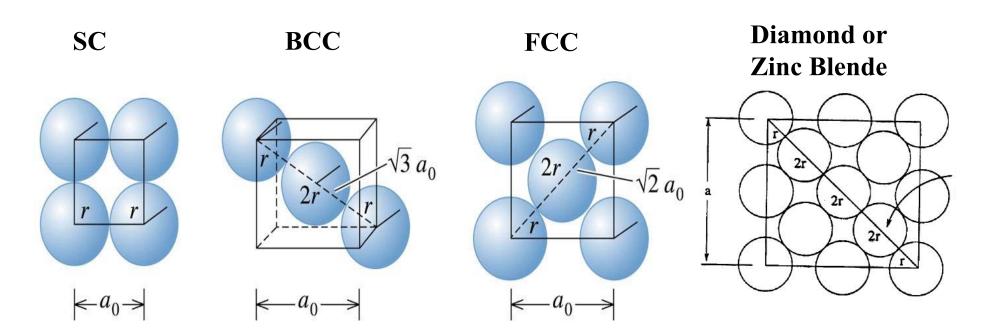
Simple Cubic Example



$$\frac{\text{Volume of atoms}}{\text{Volume of the unit cell}} = \frac{\frac{4}{3} \pi r^3}{a^3} = \frac{\frac{4}{3} \pi (\frac{a}{2})^3}{a^3} = \frac{\pi}{6} = 52\%$$

	Radius	Atoms/ unit cell	Packing Density
Simple Cubic	$\frac{a}{2}$	1	$\frac{\pi}{6} = 52\%$

Maximum radius of the atom and packing density



Maximum radius of the atom:

$$r = a_0/2$$

Packing density fraction:

6

 π

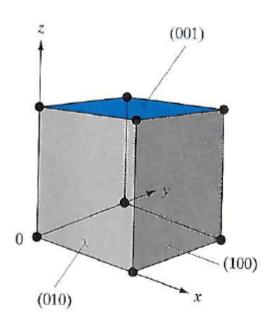
Miller index of crystal plane

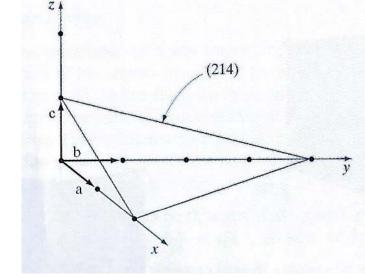
1. Locate the intercepts of the desired plane with the coordinate axes.

2. Take the reciprocal of the intercepts and reduce these to the smallest

set of integers *h,k,l*.

3. Label the plane (hkl)





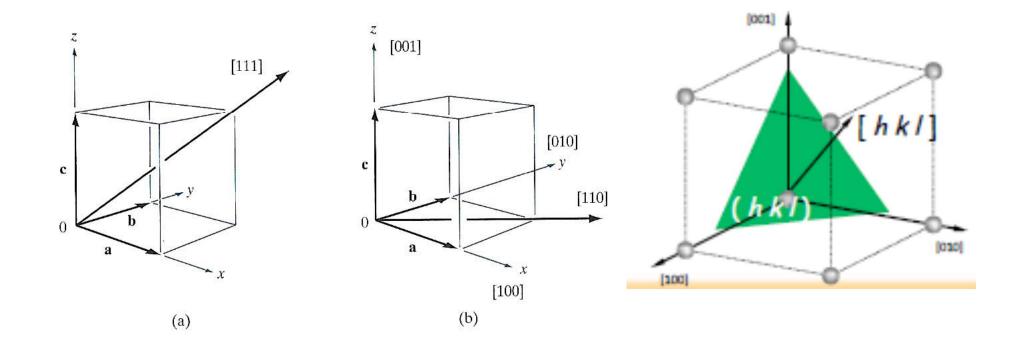
Axis	Intercept	Reciprocal
A1	2	1/2
A2	4	1/4
A3	1	1

Multiply the reciprocal numbers by 4

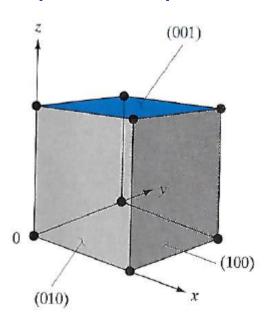
→ Miller indices (214)

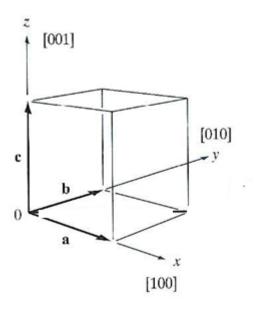
Miller index of direction

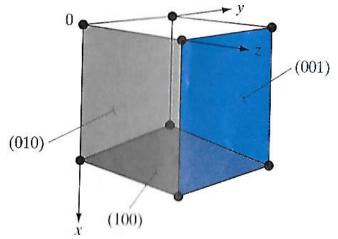
• Direction: is expressed as a set of 3 integers with same relationship as the components of a vector in that direction.



• Equivalent planes and directions:

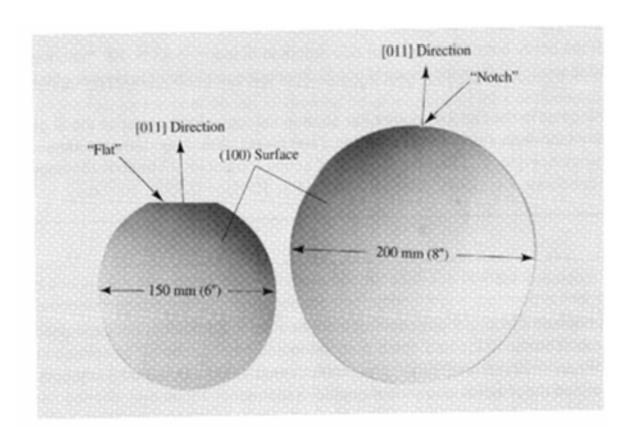






Notation	Interpretation	
(hkl)	crystal plane	
$\{hkl\}$	equivalent planes	
[hkl]	crystal direction	
< h k l >	equivalent directions	

 Si wafers usually cut along {100} plane with a notch or flat side to orient the wafer during fabrication



Key points in chapter 1 Crystal properties

- 1. The conductivity of semiconductor is in between insulator and metal.
- 2. Primitive cell is the smallest unit cell, only has lattice point at the corners; unit cell allows lattice points not only at the corners, but also at the face or body centers.
- 3. Three type of cubic lattice structure: simple cubic (sc), body-centered cubic (bcc) and face-centered cubic (fcc)
- 4. Crystal plane and directions are denoted by Miller indices (hkl) and [hkl]; Equivalent planes and directions are denoted by {hkl} and <hkl>.
- 5. Diamond structure and zinc blende structure: fcc lattice with an extra atom places at $\mathbf{a}/4+\mathbf{b}/4+\mathbf{c}/4$ from each of the fcc atoms.

If the atoms are all similar: diamond structure.

If the atoms differ on alternating sites: Zinc blende structure.

Basic units

Elementary charge (e or q): 1.602×10^{-19} C

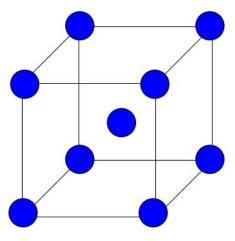
Electron volt (eV) is the amount of energy gained (or lost) by the charge of a single electron moved across an electric potential difference of one volt.

$$1eV=1.6x10^{-19}C*V=1.6x10^{-19}J$$

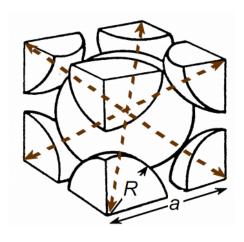
Example 1

What is the atomic density of a BCC material with lattice constant

5.2 angstroms?



Example 2

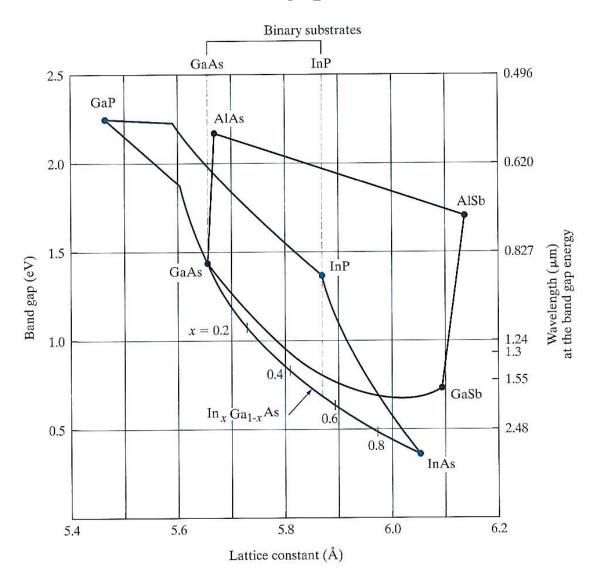


• Ex: Cr (BCC) A = 52.00 g/mol R = 0.125 nm

Avogadro's number (6.023 x 10²³ atoms/mol)

What is the mass density?

Band gap and lattice constant



 $In_xGa_{1-x}As$